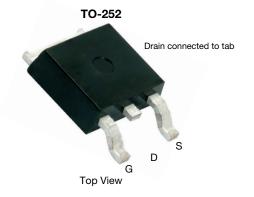


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Automotive N-Channel 150 V (D-S) 175 °C MOSFET

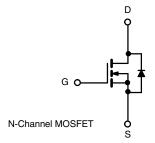
PRODUCT SUMMARY				
V _{DS} (V)	150			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.052			
I _D (A)	25			
Configuration	Single			
Package	TO-252			



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V_{DS}	150	V			
Gate-Source Voltage	V_{GS}	± 20	V			
Continuous Drain Current	T _C = 25 °C	I-	25			
	T _C = 125 °C	l _D	16			
Continuous Source Current (Diode Conduc	I _S	50	Α			
Pulsed Drain Current ^b	I _{DM}	63				
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	30			
Single Pulse Avalanche Energy	L=0.1 IIII	E _{AS}	45	mJ		
Maximum Power Dissipation ^b	T _C = 25 °C	D.	107	W		
	T _C = 125 °C	- P _D	35	, vv		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount c	R_{thJA}	50	°C/W	
Junction-to-Case (Drain)		R_{thJC}	1.4	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).



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SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		150	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.5	3	4	ľ	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 150 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 150 V, T _J = 125 °C	-	-	50	μΑ	
		$V_{GS} = 0 V$	V _{DS} = 150 V, T _J = 175 °C	-	-	250		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α	
		V _{GS} = 10 V	I _D = 15 A	-	0.038	0.052		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.104	Ω	
		V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.136		
Forward Transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 15 A	-	33	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			1	1760	2200		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	ı	215	270	pF	
Reverse Transfer Capacitance	C _{rss}			1	97	125		
Total Gate Charge ^c	Q_g			ı	34	51		
Gate-Source Charge ^c	Q_{gs}	$V_{GS} = 10 \text{ V}$	$V_{DS} = 75 \text{ V}, I_{D} = 25 \text{ A}$	-	14.5	-	nC	
Gate-Drain Charge ^c	Q_{gd}			1	5.4	-	1	
Gate Resistance	R_g		f = 1 MHz		1.0	3.2	Ω	
Turn-On Delay Time ^c	t _{d(on)}				11	17		
Rise Time ^c	t _r	V_{DD} = 75 V, R_L = 3 Ω I_D \cong 25 A, V_{GEN} = 10 V, R_g = 1 Ω		-	21	33	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	20	30		
Fall Time ^c	t _f			ı	12	20		
Source-Drain Diode Ratings and Characteristics ^b								
Pulsed Current ^a	I _{SM}			-		63	Α	
Forward Voltage	V _{SD}	I _F = 20 A, V _{GS} = 0 V		-	0.87	1.5	V	

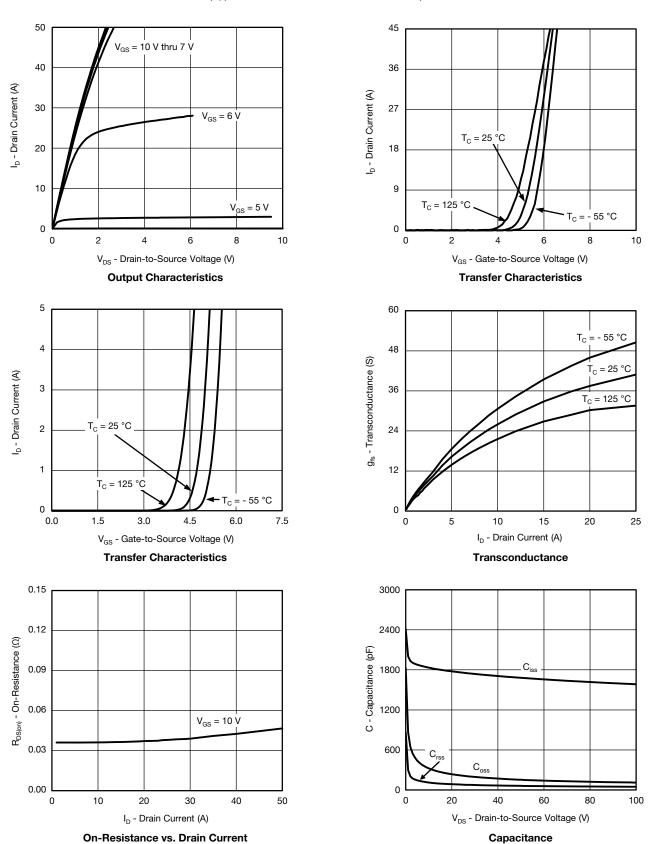
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

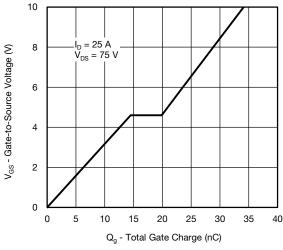


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

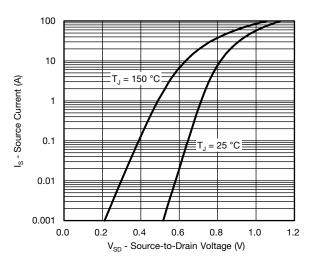




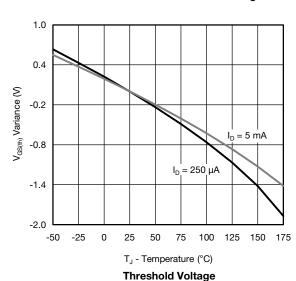
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

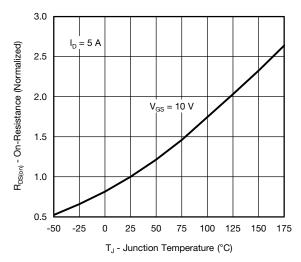


Gate Charge

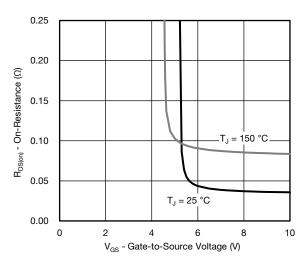


Source Drain Diode Forward Voltage

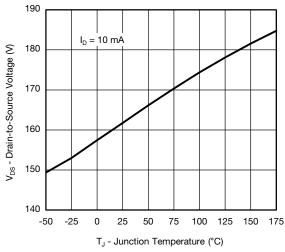




On-Resistance vs. Junction Temperature



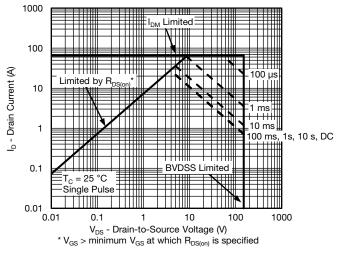
On-Resistance vs. Gate-to-Source Voltage



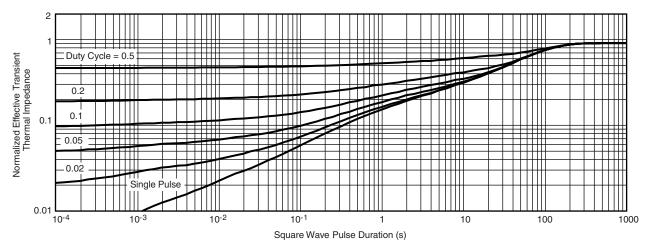
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



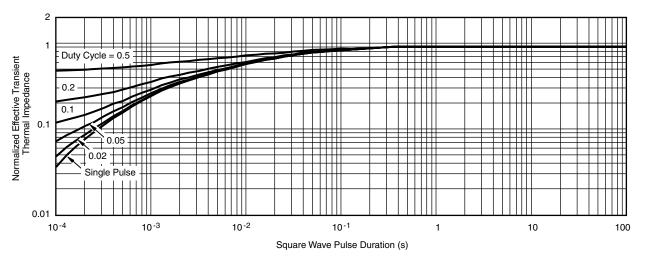
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to- Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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REVISION	HISTORY a	
REVISION	DATE	DESCRIPTION OF CHANGE
G	08-Aug-15	R _g , C _{rss} , t _r and t _f changed

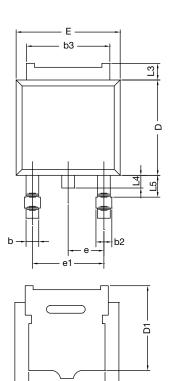
Note

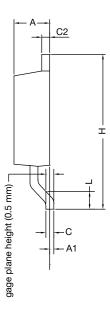
a. As of April 2014



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TO-252AA Case Outline





	MILLIN	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019					

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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